HF30-28S

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI HF30-28S** is a 28 V epitaxial RF NPN planar transistor designed primarily for SSB communications. The device utilizes emitter ballasting for improved ruggedness and reliability.

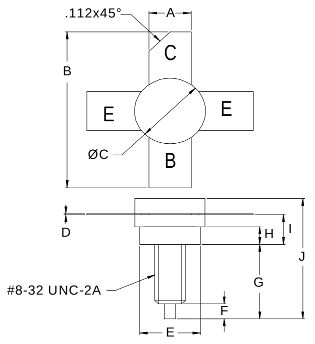
FEATURES:

- **P_G** = 20 dB min. at 30 W/30 MHz
- **IMD_3** = -30 dBc max. at 30 W(PEP)
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CB}	65 V
V_{CE}	35 V
V_{EBO}	4.0 V
P_{DISS}	60 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.9 °C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10605

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 10 mA	65		---	**V**
BV_{CES}	I_C = 200 mA	65		---	**V**
BV_{CEO}	I_C = 200 mA	35		---	**V**
BV_{EBO}	I_E = 10 mA	4.0		---	**V**
I_{CES}	V_{CE} = 30 V	---		10	**mA**
I_{CBO}	V_{CE} = 30 V	---		100	**mA**
h_{FE}	V_{CE} = 5.0 V I_C = 500 mA	5.0		200	**---**
C_{OB}	V_{CB} = 30V f = 1.0 MHz	---		65	**pF**

G_P	V_{CE} = 28 V P_{IN} = 0.48 W f = 30 MHz P_{OUT} = 30 W(PEP)	718			**dB**
η_C		60			**%**
IMD_3				-28	**dBc**